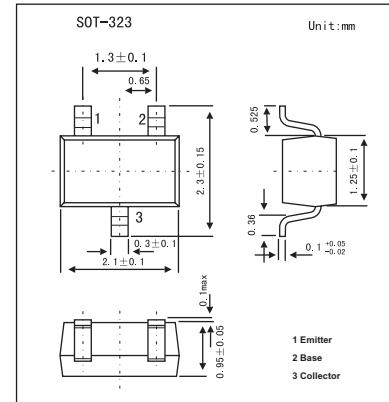


## NPN General Purpose Transistor

**BC846W, BC847W, BC848W**

### ■ Features

- Low current (max. 100 mA).
- Low voltage (max. 65 V).



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	BC846W	BC847W	BC848W	Unit
Collector-base voltage	$V_{CBO}$	80	50	30	V
Collector-emitter voltage	$V_{CEO}$	65	45	30	V
Emitter-base voltage	$V_{EBO}$	6	6	5	V
Collector current	$I_C$	100			mA
Peak collector current	$I_{CM}$	200			mA
Peak base current	$I_{BM}$	200			mA
Total power dissipation	$P_{tot}$	200			mW
Junction temperature	$T_j$	150			$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +150			$^\circ\text{C}$
Operating ambient temperature	$T_{amb}$	-65 to +150			$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th j-a}$	625			K/W

**BC846W,BC847W,BC848W**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0			15	nA
	I <sub>CBO</sub>	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C			5	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0			100	nA
DC current gain	h <sub>FE</sub>	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	110		450	
			110		800	
			110	180	220	
			200	290	450	
			420	520	800	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA		90	250	mV
		I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; *		200	600	mV
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA		700		mV
		I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; *		900		mV
Base-emitter voltage	V <sub>BE</sub>	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	580	660	700	mV
		I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V			770	mV
Collector capacitance	C <sub>c</sub>	V <sub>CB</sub> = 10 V; I <sub>E</sub> = I <sub>e</sub> = 0; f = 1 MHz			3	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz	100			MHz
Noise figure	NF	I <sub>C</sub> = 200 μA; V <sub>CE</sub> = 5 V; R <sub>S</sub> = 2 kΩ; f = 1 kHz; B = 200 Hz			10	dB

\* Pulse test: t<sub>p</sub> ≤ 300μs, δ ≤ 0.02.

## ■ hFE Classification

TYPE	BC846W	BC846AW	BC846BW
Marking	1D	1A	1B

TYPE	BC847W	BC847AW	BC847BW	BC847CW
Marking	1H	1E	1F	1G

TYPE	BC848W
Marking	1M